

BFP183E7764HTSA1 Datasheet



| | |
|------------------------------|---|
| DiGi Electronics Part Number | BFP183E7764HTSA1-DG |
| Manufacturer | Infineon Technologies |
| Manufacturer Product Number | BFP183E7764HTSA1 |
| Description | RF TRANS NPN 12V 8GHZ SOT143-4 |
| Detailed Description | RF Transistor NPN 12V 65mA 8GHz 250mW Surface Mount PG-SOT-143-3D |



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Purchase and inquiry

Manufacturer Product Number:

BFP183E7764HTSA1

Series:

-

Transistor Type:

NPN

Frequency - Transition:

8GHz

Gain:

22dB

DC Current Gain (hFE) (Min) @ Ic, Vce:

70 @ 15mA, 8V

Operating Temperature:

150°C (TJ)

Package / Case:

TO-253-4, TO-253AA

Base Product Number:

BFP183

Manufacturer:

Infineon Technologies

Product Status:

Active

Voltage - Collector Emitter Breakdown (Max):

12V

Noise Figure (dB Typ @ f):

0.9dB ~ 1.4dB @ 900MHz ~ 1.8GHz

Power - Max:

250mW

Current - Collector (Ic) (Max):

65mA

Mounting Type:

Surface Mount

Supplier Device Package:

PG-SOT-143-3D

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

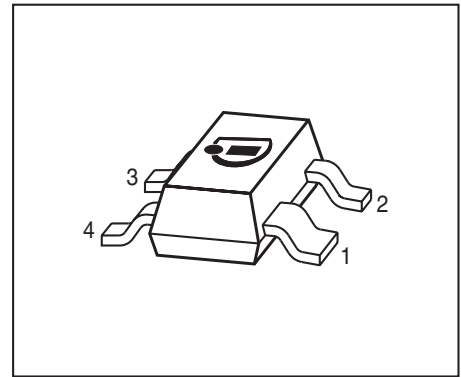
EAR99



BFP183

Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- $f_T = 8$ GHz, $NF_{\min} = 0.9$ dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

| Type | Marking | Pin Configuration | | | | | | Package |
|--------|---------|-------------------|-----|-----|-----|---|---|---------|
| BFP183 | RHs | 1=C | 2=E | 3=B | 4=E | - | - | SOT143 |

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|-----------|-------------|------|
| Collector-emitter voltage | V_{CEO} | 12 | V |
| Collector-emitter voltage | V_{CES} | 20 | |
| Collector-base voltage | V_{CBO} | 20 | |
| Emitter-base voltage | V_{EBO} | 2 | |
| Collector current | I_C | 65 | mA |
| Base current | I_B | 5 | |
| Total power dissipation ¹⁾ $T_S \leq 76$ °C | P_{tot} | 250 | mW |
| Junction temperature | T_J | 150 | °C |
| Storage temperature | T_{Stg} | -55 ... 150 | |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|------------|-------|------|
| Junction - soldering point ²⁾ | R_{thJS} | 295 | K/W |

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)


Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

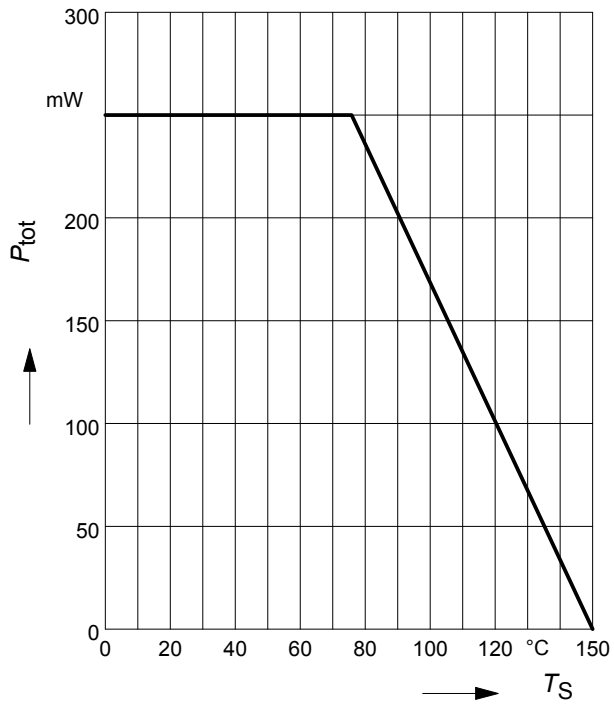
| Parameter | Symbol | Values | | | Unit |
|---|---------------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$ | $V_{(BR)CEO}$ | 12 | - | - | V |
| Collector-emitter cutoff current $V_{CE} = 20\text{ V}, V_{BE} = 0$ | I_{CES} | - | - | 100 | μA |
| Collector-base cutoff current $V_{CB} = 10\text{ V}, I_E = 0$ | I_{CBO} | - | - | 100 | nA |
| Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$ | I_{EBO} | - | - | 1 | μA |
| DC current gain $I_C = 15\text{ mA}, V_{CE} = 8\text{ V}, \text{pulse measured}$ | h_{FE} | 70 | 100 | 140 | - |


Electrical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|---------------|--------|--------------|------|------|
| | | min. | typ. | max. | |
| AC Characteristics (verified by random sampling) | | | | | |
| Transition frequency $I_C = 25\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$ | f_T | 6 | 8 | - | GHz |
| Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded | C_{cb} | - | 0.3 | 0.5 | pF |
| Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded | C_{ce} | - | 0.27 | - | |
| Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded | C_{eb} | - | 1.1 | - | |
| Minimum noise figure $I_C = 5\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$ | NF_{min} | - | 0.9 1.4 | - | dB |
| Power gain, maximum stable ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$ | G_{ms} | - | 22 | - | dB |
| Power gain, maximum available ¹⁾ $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$ | G_{ma} | - | 15.5 | - | dB |
| Transducer gain $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$ | $ S_{21e} ^2$ | - | 17.5 11.5 | - | dB |

¹⁾ $G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$, $G_{ms} = |S_{21} / S_{12}|$

Total power dissipation $P_{\text{tot}} = f(T_S)$

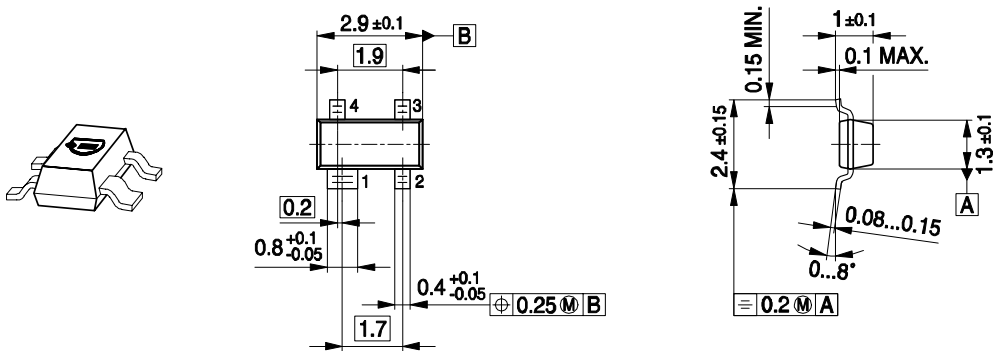




Package SOT143

BFP183

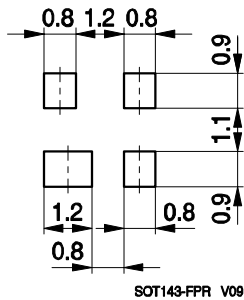
Package Outline



Note: Mold flash, protrusions or gate burrs of 0,2 mm max. per side are not included

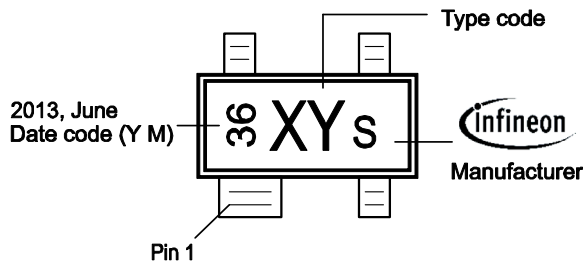
SOT143-PO V09

Foot Print



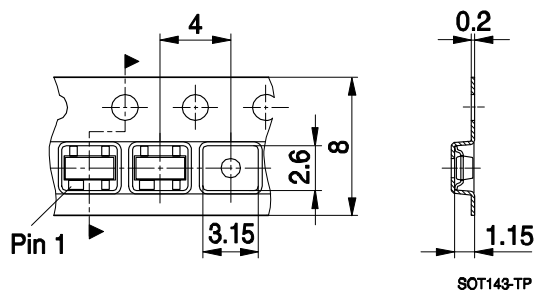
SOT143-FPR V09

Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



SOT143-TP



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